



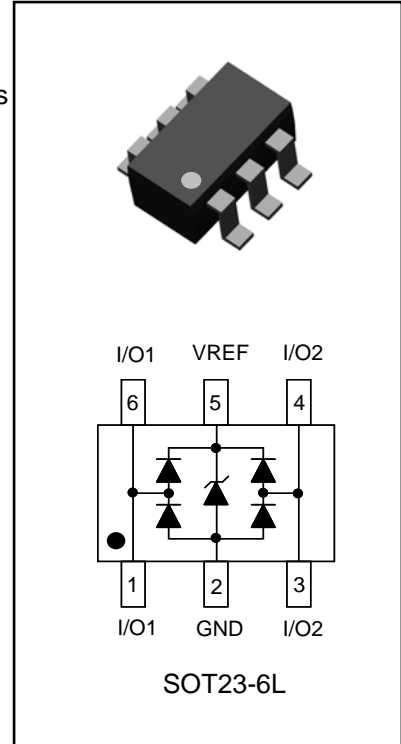
DRAFT SPEC

Low Capacitance TVS and Diode Array

This diode array is configured to protect up to two data transmission lines acting as a line terminator, minimizing overshoot and undershoot conditions due to bus impedance as well as protect against over-voltage events as electrostatic discharges. Additionally the TVS Device offers overvoltage transient protection between the operating voltage bus and ground plane.

SPECIFICATION FEATURES

- Peak Power Dissipation of 350W 8/20μs
- Maximum Capacitance of 5.0pF at 0Vdc 1MHz Line-to-Ground
- Maximum Leakage Current of 1μA @ VRWM
- Industry Standard SMT Package SOT23-6L
- IEC61000-4-2, IEC61000-4-4 and IEC61000-4-5 Full Compliance
- 100% Tin Matte finish (LEAD-FREE PRODUCT)



APPLICATIONS

- USB 2.0 and Firewire Port Protection
- LAN/WLAN Access Point terminals
- Video Signal line protection
- I²C Bus Protection



MAXIMUM RATINGS T_j = 25°C Unless otherwise noted

Rating	Symbol	Value	Units
Peak Pulse Power (8/20μs Waveform)	P _{PPM}	350	W
Peak Pulse Current (8/20μs Waveform)	I _{PP}	17.5	A
Operating Junction Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Soldering Temperature, t max = 10s	T _L	260	°C



ELECTRICAL CHARACTERISTICS Tj = 25°C unless otherwise noted

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				5	V
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1mA$	6.2			V
Reverse Leakage Current	I_R	$V_R = 5V$			1	μA
Clamping Voltage (8/20 μs)	V_C	$I_{pp} = 1A$			9.5	V
Clamping Voltage (8/20 μs)	V_C	$I_{pp} = 10A$			12	V
Clamping Voltage (8/20 μs)	V_C	$I_{pp} = 17.5A$			20	V
Off State Junction Capacitance	C_j	0 Vdc Bias f = 1MHz Between I/O pins and GND			4.0	pF
		0 Vdc Bias f = 1MHz Between I/O pins			2.5	pF

DRAFT SPEC



PACKAGE DIMENSIONS

DRAFT SPEC

